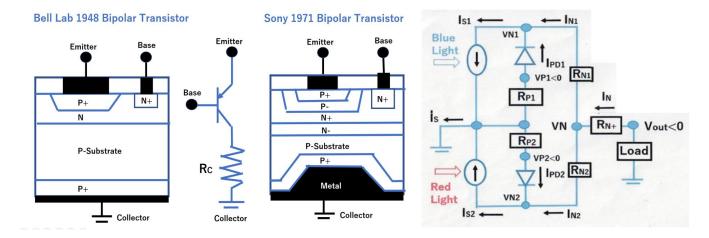
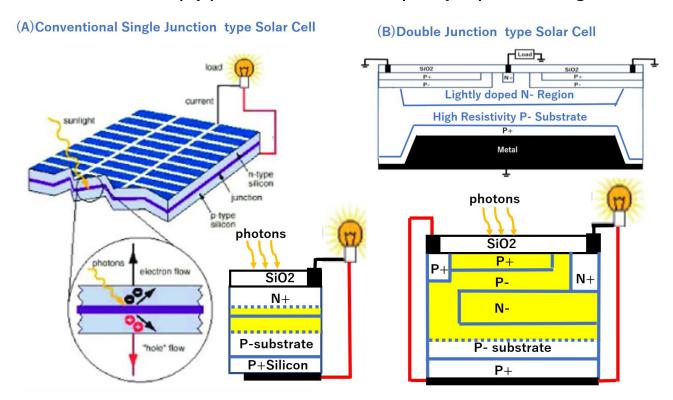
https://eds.ieee.org/images/files/newsletters/Newsletter_Jan23.pdf

The short-wave blue-light has a very short silicon-penetration depth. In the case of the conventional floating-surface N+PP+ single junction type solar cell, the N+ region surface-potential is flat and the photo electron-and-hole pairs are recombined and wasted as heat.



However, in case of the pinned surface double junction type solar cell, the surface P+P doping variation creates the surface conduction-band bending which enhances the photo electron-and hole separation at the short wave length of 400 nm range and also with completely depleted lightly doped buried N-region, separated photo electrons are directed swiftly to the small N+ outlet diffusion region by the strong electric field in the empty potential well in the completely depleted N- region.



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